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ADDITIONAL TECHNOLOGIES BY THESE INVENTORS

- ▶ Etching Technique for the Fabrication of Thin (Al, In, Ga)N Layers
- ▶ Lateral Growth Method for Defect Reduction of Semipolar Nitride Films
- ▶ Vertical Cavity Surface-Emitting Lasers with Continuous Wave Operation
- ▶ Aluminum-cladding-free Nonpolar III-Nitride LEDs and LDs
- ▶ Defect Reduction in GaN films using in-situ SiNx Nanomask
- ▶ Enhanced Light Extraction LED with a Tunnel Junction Contact Wafer Bonded to a Conductive Oxide
- ▶ Transparent Mirrorless (TML) LEDs
- ▶ Optimization of Laser Bar Orientation for Nonpolar Laser Diodes
- ▶ Improved Fabrication of Nonpolar InGaN Thin Films, Heterostructures, and Devices
- ▶ Growth of High-Quality, Thick, Non-Polar M-Plane GaN Films
- ▶ High-Efficiency, Mirrorless Non-Polar and Semi-Polar Light Emitting Devices
- ▶ Technique for the Nitride Growth of Semipolar Thin Films, Heterostructures, and Semiconductor Devices
- ▶ MOCVD Growth of Planar Non-Polar M-Plane Gallium Nitride
- ▶ Methods for Fabricating III-Nitride Tunnel Junction Devices
- ▶ Contact Architectures for Tunnel Junction Devices
- ▶ Semi-polar LED/LD Devices on Relaxed Template with Misfit Dislocation at Hetero-interface
- ▶ Semipolar-Based Yellow, Green, Blue LEDs with Improved Performance
- ▶ Growth of Semipolar III-V Nitride Films with Lower Defect Density
- ▶ III-Nitride Tunnel Junction LED with High Wall Plug Efficiency
- ▶ Cleaved Facet Edge-Emitting Laser Diodes Grown on Semipolar GaN
- ▶ Growth of High-Performance M-plane GaN Optical Devices
- ▶ Improved Anisotropic Strain Control in Semipolar Nitride Devices
- ▶ Method for Increasing GaN Substrate Area in Nitride Devices
- ▶ Limiting Strain-Relaxation in III-Nitride Heterostructures by Substrate Patterning
- ▶ Growth of Planar Semi-Polar Gallium Nitride
- ▶ Defect Reduction of Non-Polar and Semi-Polar III-Nitrides

